

CPC COOPERATIVE PATENT CLASSIFICATION

C CHEMISTRY; METALLURGY

(NOTES omitted)

METALLURGY

C30 CRYSTAL GROWTH

C30B SINGLE-CRYSTAL GROWTH (by using ultra-high pressure, e.g. for the formation of diamonds, [B01J 3/06](#)); **UNIDIRECTIONAL SOLIDIFICATION OF EUTECTIC MATERIAL OR UNIDIRECTIONAL DEMIXING OF EUTECTOID MATERIAL; REFINING BY ZONE-MELTING OF MATERIAL** (zone-refining of metals or alloys [C22B](#)); **PRODUCTION OF A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (casting of metals, casting of other substances by the same processes or devices [B22D](#); working of plastics [B29](#); modifying the physical structure of metals or alloys [C21D](#), [C22F](#)); **SINGLE CRYSTALS OR HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE; AFTER-TREATMENT OF SINGLE CRYSTALS OR A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (for producing semiconductor devices or parts thereof [H01L](#), [H10](#)); **APPARATUS THEREFOR**

NOTES

- In this subclass, the following expressions are used with the meaning indicated:
 - "single-crystal" includes also twin crystals and a predominantly single crystal product;
 - "homogeneous polycrystalline material" means a material with crystal particles, all of which have the same chemical composition;
 - "defined structure" means the structure of a material with grains which are oriented in a preferential way or have larger dimensions than normally obtained.
- In this subclass:
 - the preparation of crystals or a homogeneous polycrystalline material with defined structure of particular materials or shapes is classified in the group for the process as well as in group [C30B 29/00](#);
 - an apparatus specially adapted for a specific process is classified in the appropriate group for the process. Apparatus to be used in more than one kind of process is classified in group [C30B 35/00](#).

WARNING

In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

Single-crystal growth from solids or gels

5/02 . with addition of doping materials

- 1/00 Single-crystal growth directly from the solid state** (unidirectional demixing of eutectoid materials [C30B 3/00](#); under a protective fluid [C30B 27/00](#))
- 1/02 . by thermal treatment, e.g. strain annealing ([C30B 1/12](#) takes precedence)
- 1/023 . . {from solids with amorphous structure}
- 1/026 . . {Solid phase epitaxial growth through a disordered intermediate layer}
- 1/04 . . Isothermal recrystallisation
- 1/06 . . Recrystallisation under a temperature gradient
- 1/08 . . . Zone recrystallisation
- 1/10 . by solid state reactions or multi-phase diffusion
- 1/12 . by pressure treatment during the growth
- 3/00 Unidirectional demixing of eutectoid materials**
- 5/00 Single-crystal growth from gels** (under a protective fluid [C30B 27/00](#))

Single-crystal growth from liquids; Unidirectional solidification of eutectic materials

- 7/00 Single-crystal growth from solutions using solvents which are liquid at normal temperature, e.g. aqueous solutions** (from molten solvents [C30B 9/00](#); by normal or gradient freezing [C30B 11/00](#); under a protective fluid [C30B 27/00](#))
- 7/005 . {Epitaxial layer growth}
- 7/02 . by evaporation of the solvent
- 7/04 . . using aqueous solvents
- 7/06 . . using non-aqueous solvents
- 7/08 . by cooling of the solution
- 7/10 . by application of pressure, e.g. hydrothermal processes
- 7/105 . . {using ammonia as solvent, i.e. ammonothermal processes}

7/12	• by electrolysis	13/14	• Crucibles or vessels
7/14	• the crystallising materials being formed by chemical reactions in the solution	13/16	• Heating of the molten zone
		13/18	• • the heating element being in contact with, or immersed in, the molten zone
9/00	Single-crystal growth from melt solutions using molten solvents (by normal or gradient freezing C30B 11/00 ; by zone-melting C30B 13/00 ; by crystal pulling C30B 15/00 ; on immersed seed crystal C30B 17/00 ; by liquid phase epitaxial growth C30B 19/00 ; under a protective fluid C30B 27/00)	13/20	• • by induction, e.g. hot wire technique (C30B 13/18 takes precedence)
9/02	• by evaporation of the molten solvent	13/22	• • by irradiation or electric discharge
9/04	• by cooling of the solution	13/24	• • • using electromagnetic waves
9/06	• • using as solvent a component of the crystal composition	13/26	• Stirring of the molten zone
9/08	• • using other solvents	13/28	• Controlling or regulating
9/10	• • • Metal solvents	13/285	• • {Crystal holders, e.g. chucks}
9/12	• • • Salt solvents, e.g. flux growth	13/30	• • Stabilisation or shape controlling of the molten zone, e.g. by concentrators, by electromagnetic fields; Controlling the section of the crystal
9/14	• by electrolysis	13/32	• Mechanisms for moving either the charge or the heater
		13/34	• characterised by the seed, e.g. by its crystallographic orientation
11/00	Single-crystal growth by normal freezing or freezing under temperature gradient, e.g. Bridgman-Stockbarger method (C30B 13/00 , C30B 15/00 , C30B 17/00 , C30B 19/00 take precedence; under a protective fluid C30B 27/00)	15/00	Single-crystal growth by pulling from a melt, e.g. Czochralski method (under a protective fluid C30B 27/00)
11/001	• {Continuous growth}	15/002	• {Continuous growth}
11/002	• {Crucibles or containers for supporting the melt}	15/005	• {Simultaneous pulling of more than one crystal}
11/003	• {Heating or cooling of the melt or the crystallised material}	15/007	• {Pulling on a substrate}
11/005	• {by irradiation or electric discharge}	15/02	• adding crystallising materials or reactants forming it <u>in situ</u> to the melt
11/006	• {Controlling or regulating}	15/04	• • adding doping materials, e.g. for n-p-junction
11/007	• {Mechanisms for moving either the charge or the heater}	15/06	• Non-vertical pulling
11/008	• {using centrifugal force to the charge}	15/08	• Downward pulling
11/02	• without using solvents (C30B 11/06 takes precedence)	15/10	• Crucibles or containers for supporting the melt
11/04	• adding crystallising materials or reactants forming it <u>in situ</u> to the melt	15/12	• • Double crucible methods
11/06	• • at least one but not all components of the crystal composition being added	15/14	• Heating of the melt or the crystallised materials
11/065	• • • {before crystallising, e.g. synthesis}	15/16	• • by irradiation or electric discharge
11/08	• • every component of the crystal composition being added during the crystallisation	15/18	• • using direct resistance heating in addition to other methods of heating, e.g. using Peltier heat
11/10	• • • Solid or liquid components, e.g. Verneuil method	15/20	• Controlling or regulating (controlling or regulating in general G05)
11/12	• • • Vaporous components, e.g. vapour-liquid-solid-growth	15/203	• • {the relationship of pull rate (v) to axial thermal gradient (G)}
11/14	• characterised by the seed, e.g. its crystallographic orientation	15/206	• • {the thermal history of growing the ingot}
		15/22	• • Stabilisation or shape controlling of the molten zone near the pulled crystal; Controlling the section of the crystal
13/00	Single-crystal growth by zone-melting; Refining by zone-melting (C30B 17/00 takes precedence ; by changing the cross-section of the treated solid C30B 15/00 ; under a protective fluid C30B 27/00 ; zone-refining of specific materials, see the relevant subclasses for the materials)	15/24	• • • using mechanical means, e.g. shaping guides (shaping dies for edge-defined film-fed crystal growth C30B 15/34)
13/005	• {Continuous growth}	15/26	• • • using television detectors; using photo or X-ray detectors
13/02	• Zone-melting with a solvent, e.g. travelling solvent process	15/28	• • • using weight changes of the crystal or the melt, e.g. flotation methods
13/04	• Homogenisation by zone-levelling	15/30	• Mechanisms for rotating or moving either the melt or the crystal (flotation methods C30B 15/28)
13/06	• the molten zone not extending over the whole cross-section	15/305	• • {Stirring of the melt}
13/08	• adding crystallising materials or reactants forming it <u>in situ</u> to the molten zone	15/32	• Seed holders, e.g. chucks
13/10	• • with addition of doping materials	15/34	• Edge-defined film-fed crystal-growth using dies or slits
13/12	• • • in the gaseous or vapour state	15/36	• characterised by the seed, e.g. its crystallographic orientation
		17/00	Single-crystal growth onto a seed which remains in the melt during growth, e.g. Nacken-Kyropoulos method (C30B 15/00 takes precedence)
		19/00	Liquid-phase epitaxial-layer growth

19/02	. using molten solvents, e.g. flux	25/16	. . Controlling or regulating (controlling or regulating in general G05)
19/04	. . the solvent being a component of the crystal composition	25/165	. . . {the flow of the reactive gases}
19/06	. Reaction chambers; Boats for supporting the melt; Substrate holders	25/18	. . characterised by the substrate
19/061	. . {Tipping system, e.g. by rotation}	25/183	. . . {being provided with a buffer layer, e.g. a lattice matching layer}
19/062	. . {Vertical dipping system}	25/186	. . . {being specially pre-treated by, e.g. chemical or physical means}
19/063	. . {Sliding boat system}	25/20	. . . the substrate being of the same materials as the epitaxial layer
19/064	. . {Rotating sliding boat system}	25/205 {the substrate being of insulating material}
19/065	. . {Multiple stacked slider system}	25/22	. . Sandwich processes
19/066	. . {Injection or centrifugal force system}	27/00	Single-crystal growth under a protective fluid
19/067	. . {Boots or containers}	27/02	. by pulling from a melt
19/068	. . {Substrate holders}	28/00	Production of homogeneous polycrystalline material with defined structure
19/08	. Heating of the reaction chamber or the substrate	28/02	. directly from the solid state
19/10	. Controlling or regulating (controlling or regulating in general G05)	28/04	. from liquids
19/103	. . {Current controlled or induced growth}	28/06	. . by normal freezing or freezing under temperature gradient
19/106	. . {adding crystallising material or reactants forming it <i>in situ</i> to the liquid}	28/08	. . by zone-melting
19/12	. characterised by the substrate	28/10	. . by pulling from a melt
21/00	Unidirectional solidification of eutectic materials	28/12	. directly from the gas state
21/02	. by normal casting or gradient freezing	28/14	. . by chemical reaction of reactive gases
21/04	. by zone-melting	29/00	Single crystals or homogeneous polycrystalline material with defined structure characterised by the material or by their shape
21/06	. by pulling from a melt		NOTE
Single-crystal growth from vapours			In groups C30B 29/02 - C30B 29/58 , in the absence of an indication to the contrary, a material is classified in the last appropriate place.
23/00	Single-crystal growth by condensing evaporated or sublimed materials		
	NOTE		
	Groups C30B 23/002 - C30B 23/005 take precedence over groups C30B 23/007 - C30B 23/08		
23/002	. {Controlling or regulating}	29/02	. Elements
23/005	. . {Controlling or regulating flux or flow of depositing species or vapour}	29/04	. . Diamond
23/007	. {Growth of whiskers or needles}	29/06	. . Silicon
23/02	. Epitaxial-layer growth	29/08	. . Germanium
23/025	. . {characterised by the substrate}	29/10	. Inorganic compounds or compositions
23/04	. . Pattern deposit, e.g. by using masks	29/12	. . Halides
23/06	. . Heating of the deposition chamber, the substrate or the materials to be evaporated	29/14	. . Phosphates
23/063	. . . {Heating of the substrate}	29/16	. . Oxides
23/066	. . . {Heating of the material to be evaporated}	29/18	. . . Quartz
23/08	. . by condensing ionised vapours (by reactive sputtering C30B 25/06)	29/20	. . . Aluminium oxides
25/00	Single-crystal growth by chemical reaction of reactive gases, e.g. chemical vapour-deposition growth	29/22	. . . Complex oxides
25/005	. {Growth of whiskers or needles}	29/225 {based on rare earth copper oxides, e.g. high T-superconductors}
25/02	. Epitaxial-layer growth	29/24 with formula $AMeO_3$, wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. ortho ferrites
25/025	. . {Continuous growth}	29/26 with formula BMe_2O_4 , wherein B is Mg, Ni, Co, Al, Zn, or Cd and Me is Fe, Ga, Sc, Cr, Co, or Al
25/04	. . Pattern deposit, e.g. by using masks	29/28 with formula $A_3Me_5O_{12}$ wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. garnets
25/06	. . by reactive sputtering	29/30 Niobates; Vanadates; Tantalates
25/08	. . Reaction chambers; Selection of materials therefor	29/32 Titanates; Germanates; Molybdates; Tungstates
25/10	. . Heating of the reaction chamber or the substrate	29/34	. . Silicates
25/105	. . . {by irradiation or electric discharge}	29/36	. . Carbides
25/12	. . Substrate holders or susceptors	29/38	. . Nitrides
25/14	. . Feed and outlet means for the gases; Modifying the flow of the reactive gases		

- 29/40 . . $A_{III}B_V$ compounds {wherein A is B, Al, Ga, In or Tl and B is N, P, As, Sb or Bi}
- 29/403 . . . { A_{III} -nitrides}
- 29/406 . . . {Gallium nitride}
- 29/42 . . . Gallium arsenide
- 29/44 . . . Gallium phosphide
- 29/46 . . Sulfur-, selenium- or tellurium-containing compounds
- 29/48 . . . $A_{II}B_{VI}$ compounds {wherein A is Zn, Cd or Hg, and B is S, Se or Te}
- 29/50 Cadmium sulfide
- 29/52 . . Alloys
- 29/54 . Organic compounds
- 29/56 . . Tartrates
- 29/58 . . Macromolecular compounds
- 29/60 . characterised by shape
- 29/602 . . {Nanotubes}
- 29/605 . . {Products containing multiple oriented crystallites, e.g. columnar crystallites}
- 29/62 . . Whiskers or needles
- 29/64 . . Flat crystals, e.g. plates, strips or discs
- 29/66 . . Crystals of complex geometrical shape, e.g. tubes, cylinders
- 29/68 . . Crystals with laminate structure, e.g. "superlattices"

30/00 Production of single crystals or homogeneous polycrystalline material with defined structure characterised by the action of electric or magnetic fields, wave energy or other specific physical conditions

NOTE

When classifying in this group, classification is also made in groups [C30B 1/00](#) - [C30B 27/00](#) according to the process of crystal growth.

- 30/02 . using electric fields, e.g. electrolysis
- 30/04 . using magnetic fields
- 30/06 . using mechanical vibrations
- 30/08 . in conditions of zero-gravity or low gravity

After-treatment of single crystals or homogeneous polycrystalline material with defined structure

- 31/00 Diffusion or doping processes for single crystals or homogeneous polycrystalline material with defined structure; Apparatus therefor**
- 31/02 . by contacting with diffusion materials in the solid state
- 31/04 . by contacting with diffusion materials in the liquid state
- 31/045 . . {by electrolysis}
- 31/06 . by contacting with diffusion material in the gaseous state
- 31/08 . . the diffusion materials being a compound of the elements to be diffused
- 31/10 . . Reaction chambers; Selection of materials therefor
- 31/103 . . . {Mechanisms for moving either the charge or heater}
- 31/106 . . . {Continuous processes}
- 31/12 . . Heating of the reaction chamber
- 31/14 . . Substrate holders or susceptors

- 31/16 . . Feed and outlet means for the gases; Modifying the flow of the gases
- 31/165 . . . {Diffusion sources}
- 31/18 . . Controlling or regulating
- 31/185 . . . {Pattern diffusion, e.g. by using masks}
- 31/20 . Doping by irradiation with electromagnetic waves or by particle radiation
- 31/22 . . by ion-implantation
- 33/00 After-treatment of single crystals or homogeneous polycrystalline material with defined structure ([C30B 31/00](#) takes precedence)**
- 33/005 . {Oxydation}
- 33/02 . Heat treatment ([C30B 33/04](#), [C30B 33/06](#) take precedence)
- 33/04 . using electric or magnetic fields or particle radiation
- 33/06 . Joining of crystals
- 33/08 . Etching
- 33/10 . . in solutions or melts
- 33/12 . . in gas atmosphere or plasma
- 35/00 Apparatus not otherwise provided for, specially adapted for the growth, production or after-treatment of single crystals or of a homogeneous polycrystalline material with defined structure**
- 35/002 . {Crucibles or containers}
- 35/005 . {Transport systems}
- 35/007 . {Apparatus for preparing, pre-treating the source material to be used for crystal growth}